

HiPerFET™ Power MOSFETs

IXFA 3N80 IXFP 3N80

 V_{DSS} = 800 V I_{D25} = 3.6 A $R_{DS(on)}$ = 3.6 Ω

t_{rr} ≤ **250** ns

N-Channel Enhancement Mode Avalanche Rated, Low Q_a, High dv/dt

Preliminary data sheet



Symbol	Test Conditions	Maximu	ბs um Ratings	
V _{DSS}	T _J = 25°C to 150°C	800	V	
$V_{\mathtt{DGR}}$	$T_J = 25$ °C to 150°C; $R_{GS} = 1 M\Omega$	800	V	
V _{GS}	Continuous	±20	V	
$V_{\rm GSM}$	Transient	±30	V	
I _{D25}	T _c = 25°C	3.6	Α	
I _{DM}	$T_{c} = 25$ °C, pulse width limited by T_{JM}	14.4	Α	
I _{AR}	$T_{c} = 25^{\circ}C$	3.6	Α	
E _{AR}	T _c = 25°C	10	mJ	
E _{AS}		400	mJ	
dv/dt	$\begin{array}{ll} I_{_{S}} & \leq I_{_{DM}}, \ di/dt \leq 100 \ A/\mu s, \ V_{_{DD}} \leq V_{_{DSS}}, \\ T_{_{J}} & \leq 150^{\circ} C, \ R_{_{G}} = 2 \ \Omega \end{array}$	5	V/ns	
P_{D}	T _c = 25°C	100	W	
T		-55 to +150	°C	
T _{JM}		150	°C	
T_{stg}		-55 to +150	°C	
T _L	1.6 mm (0.063 in) from case for 10 s	300	°C	
M _d	Mounting torque (TO-220)	1.13/10	Nm/lb.in.	
Weight	TO-220 TO-263	4 2	g g	

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		D (TAB)
	G D	,

TO-263 (IXFA)

TO-220 (IXFP)



G = Gate D = Drain S = Source TAB = Drain

Features

- International standard packages
- Low R_{DS (on)}
- Rated for unclamped Inductive load Switching (UIS)

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	$(T_J = 25^{\circ}C, \text{ unless})$ min.	haracter otherwis typ.		fied)
V _{DSS}	$V_{GS} = 0 \text{ V}, I_{D} = 1 \text{ mA}$ $V_{DS} = V_{GS}, I_{D} = 1 \text{ mA}$	800 2.5		4.5	V
GS(th)	$V_{DS} = V_{GS}, V_{DC} = V_{DC}$	2.0		±100	nA
Dss	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	T _J = 25°C T _J = 125°C		50 1	μA mA
R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_{D} = 0.5 I_{D25}$ Pulse test, t \le 300 \mus, duty	y cycle d≤2 %		3.6	Ω

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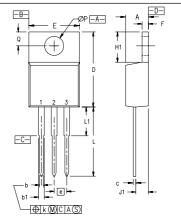
Symbol	Test Conditions Ch $(T_J = 25^{\circ}\text{C}, \text{ unless})$		istic Values se specified)
	min.	typ.	max.
g _{fs}	$V_{DS} = 20 \text{ V}; I_{D} = 0.5 \cdot I_{D25}, \text{ pulse test}$ 2.5	3.4	s
C _{iss}		685	pF
C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	73	pF
\mathbf{C}_{rss}	J	16	pF
t _{d(on)}		12	ns
t _r	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$	11	ns
$\mathbf{t}_{d(off)}$	$R_{\rm G}$ = 12 Ω (External),	25	ns
t _r	J	14	ns
$\mathbf{Q}_{g(on)}$		24	nC
\mathbf{Q}_{gs}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$	6	nC
\mathbf{Q}_{gd}	J	9	nC
R _{thJC}			1.25 KW
R _{thCK}	(TO-220)	0.25	KW

Source-Drain Diode

Characteristic Values (T₁ = 25°C, unless otherwise specified)

Symbol	Test Conditions m	in.	typ.	max.	,
I _s	V _{GS} = 0 V			3.6	Α
I _{SM}	Repetitive; pulse width limited by T_{JM}			14.4	Α
V_{SD}	$I_{_F} = I_{_S}, \ V_{_{GS}} = 0 \ V,$ Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5	V
t _{rr}	<u> </u>			250	ns
$\mathbf{Q}_{_{\mathbf{RM}}}$	$I_{\rm F} = I_{\rm S}$, -di/dt = 100 A/ μ s, $V_{\rm R} = 100 {\rm V}$		0.52		μС
I _{RM}	J		1.8		Α

TO-220 (IXFP) Outline

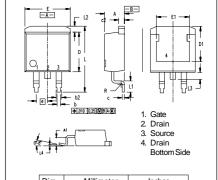


Pins: 1 - Gate 2 - Drain 3 - Source 4 - Drain Bottom Side

MYZ	INCH	IES .	S MILLIMET	
2114	MIN	MAX	MIN	MAX
Α	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
С	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
е	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØР	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline T0-220 AB.

TO-263 (IXFA) Outline



Dim.	Millimeter		Millimeter Inches	
	Min.	Max.	Min.	Max.
Α	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
С	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
Е	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
е	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029